

ZXTN25012EFH

12V, SOT23, NPN medium power transistor

Summary

$BV_{CEO} > 12V$

$BV_{ECX} > 6V$

$h_{FE} > 500$

$I_{C(cont)} = 6A$

$V_{CE(sat)} < 32mV @ 1A$

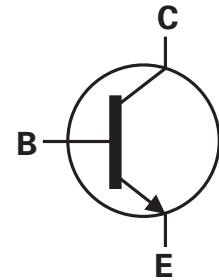
$R_{CE(sat)} = 23m\Omega$

$P_D = 1.25W$



Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

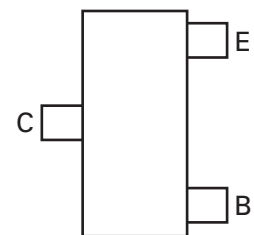


Features

- High power dissipation SOT23 package
- High peak current
- Very high gain
- Low saturation voltage
- 6V reverse blocking voltage

Applications

- MOSFET gate drivers
- Power switches
- Motor control
- DC fans
- DC-DC converters



Pinout - top view

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN25012EFHTA	7	8	3,000

Device marking

1C3

ZXTN25012EFH

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	20	V
Collector-emitter voltage	V_{CEO}	12	V
Emitter-collector voltage (reverse blocking)	V_{ECX}	6	V
Emitter-base voltage	V_{EBO}	7	V
Continuous collector current ^(c)	I_C	6	A
Base current	I_B	1	A
Peak pulse current	I_{CM}	15	A
Power dissipation at $T_{amb} = 25^{\circ}C^{(a)}$ Linear derating factor	P_D	0.73 5.84	W mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(b)}$ Linear derating factor	P_D	1.05 8.4	W mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(c)}$ Linear derating factor	P_D	1.25 9.6	W mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(d)}$ Linear derating factor	P_D	1.81 14.5	W mW/°C
Operating and storage temperature range	T_j, T_{stg}	- 55 to 150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	171	°C/W
Junction to ambient ^(b)	$R_{\theta JA}$	119	°C/W
Junction to ambient ^(c)	$R_{\theta JA}$	100	°C/W
Junction to ambient ^(d)	$R_{\theta JA}$	69	°C/W

NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

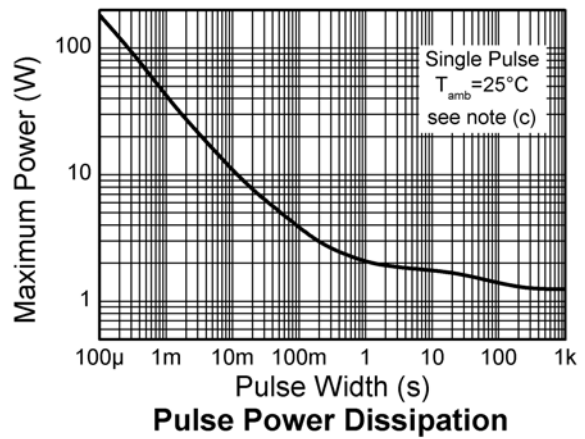
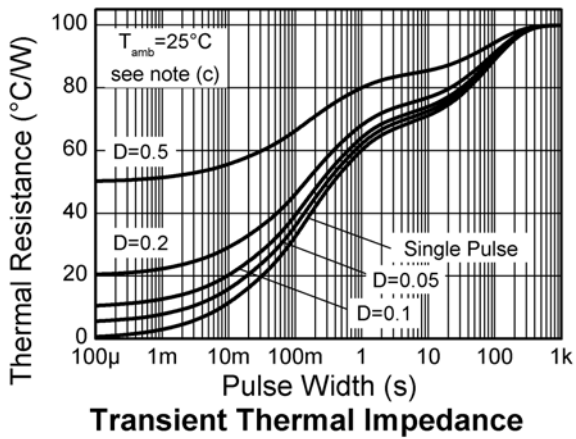
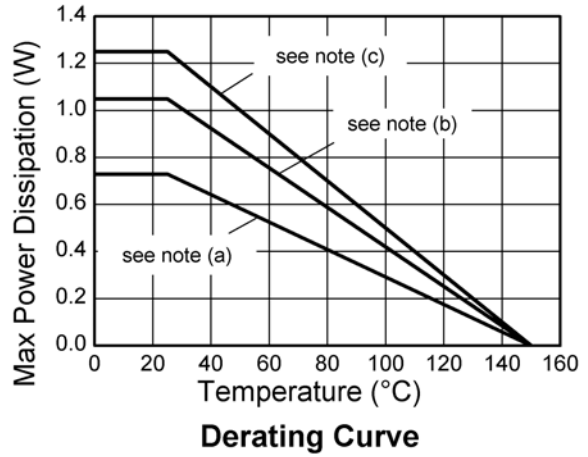
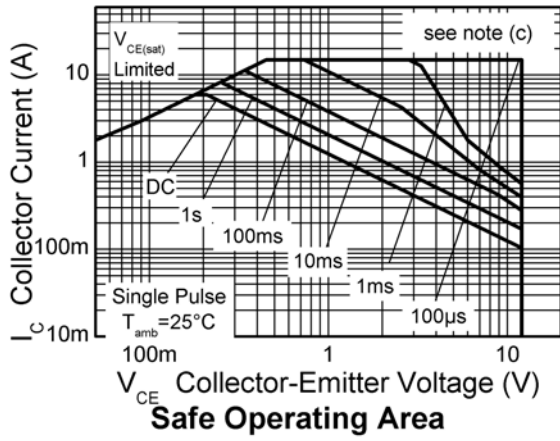
(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(d) As (c) above measured at $t < 5$ secs.

ZXTN25012EFH

Characteristics



ZXTN25012EFH

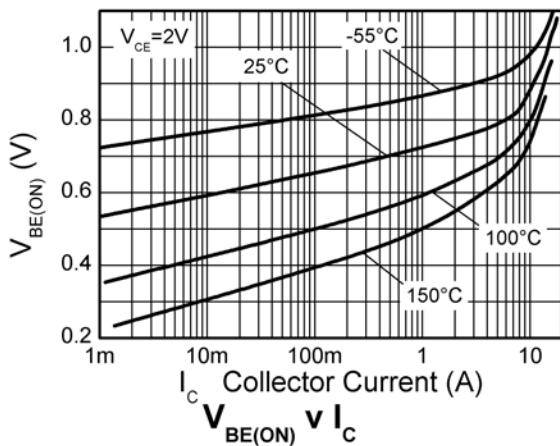
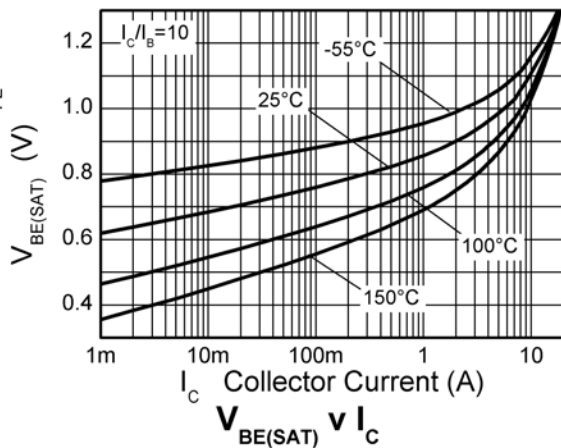
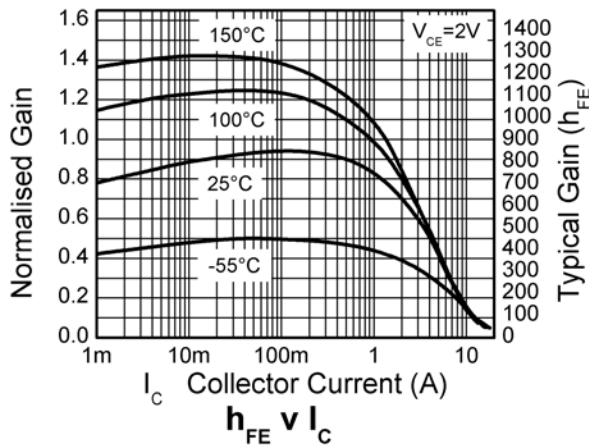
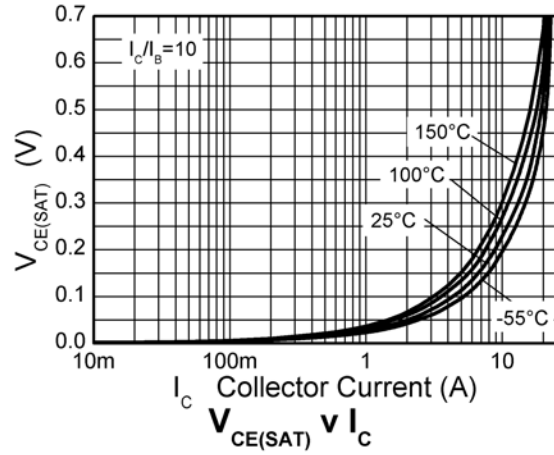
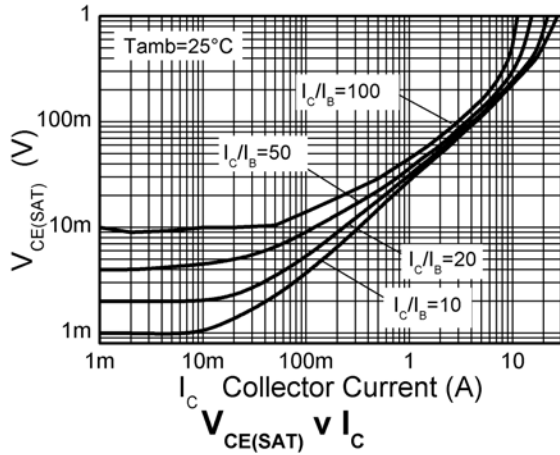
Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	20	40		V	$I_C = 100\mu\text{A}$
Collector-emitter breakdown voltage (base open)	BV_{CEO}	12	17		V	$I_C = 10\text{mA}^{(*)}$
Emitter-base breakdown voltage	BV_{EBO}	7	8.3		V	$I_E = 100\mu\text{A}$
Emitter-collector breakdown voltage (reverse blocking)	BV_{ECX}	6	8.0		V	$I_E = 100\mu\text{A}$, $R_{BC} < 1\text{k}\Omega$ or $0.25\text{V} > V_{BC} > -0.25\text{V}$
Emitter-collector breakdown voltage (base open)	BV_{ECO}	4.5	5.5		V	$I_E = 100\mu\text{A}$,
Collector-base cut-off current	I_{CBO}		<1	50 0.5	nA μA	$V_{CB} = 20\text{V}$ $V_{CB} = 20\text{V}$, $T_{amb} = 100^{\circ}\text{C}$
Emitter-base cut-off current	I_{EBO}		<1	50	nA	$V_{EB} = 5.6\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$		28 45 60 160	32 55 75 190	mV mV mV mV	$I_C = 1\text{A}$, $I_B = 100\text{mA}^{(*)}$ $I_C = 1\text{A}$, $I_B = 10\text{mA}^{(*)}$ $I_C = 2\text{A}$, $I_B = 40\text{mA}^{(*)}$ $I_C = 6\text{A}$, $I_B = 120\text{mA}^{(*)}$
Base-emitter saturation voltage	$V_{BE(sat)}$		920	1000	mV	$I_C = 6\text{A}$, $I_B = 120\text{mA}^{(*)}$
Base-emitter turn-on voltage	$V_{BE(on)}$		800	900	mV	$I_C = 6\text{A}$, $V_{CE} = 2\text{V}^{(*)}$
Static forward current transfer ratio	h_{FE}	500 500 300 40	800 750 460 55	1500		$I_C = 10\text{mA}$, $V_{CE} = 2\text{V}^{(*)}$ $I_C = 1\text{A}$, $V_{CE} = 2\text{V}^{(*)}$ $I_C = 4\text{A}$, $V_{CE} = 2\text{V}^{(*)}$ $I_C = 15\text{A}$, $V_{CE} = 2\text{V}^{(*)}$
Transition frequency	f_T		260		MHz	$I_C = 50\text{mA}$, $V_{CE} = 10\text{V}$ $f = 100\text{MHz}$
Output capacitance	C_{OBO}		25.6	35	pF	$V_{CB} = 10\text{V}$, $f = 1\text{MHz}^{(*)}$
Delay time	t_d		70.9		ns	$V_{CC} = 10\text{V}$.
Rise time	t_r		69.8		ns	$I_C = 1\text{A}$,
Storage time	t_s		233		ns	$I_{B1} = I_{B2} = 10\text{mA}$.
Fall time	t_f		71.6		ns	

NOTES:

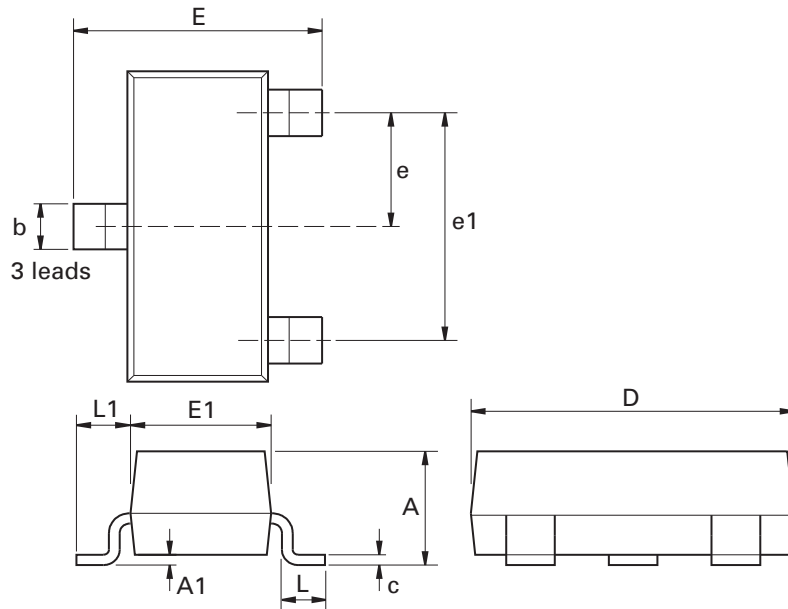
(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

Typical characteristics



ZXTN25012EFH

Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	-	1.12	-	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	E	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
c	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
e	0.95 NOM		0.037 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Kusterman-Park D-81541 München Germany	Zetex Inc 700 Veterans Memorial Highway Hauppauge, NY 11788 USA	Zetex (Asia Ltd) 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong	Zetex Semiconductors plc Zetex Technology Park, Chadderton Oldham, OL9 9LL United Kingdom
Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europe.sales@zetex.com	Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com	Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com	Telephone: (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com

For international sales offices visit www.zetex.com/offices

Zetex products are distributed worldwide. For details, see www.zetex.com/salesnetwork

This publication is issued to provide outline information only which (unless agreed by the company in writing) may not be used, applied or reproduced for any purpose or form part of any order or contact or be regarded as a representation relating to the products or services concerned. The company reserves the right to alter without notice the specification, design, price or conditions of supply of any product or service.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.